

ABSTRACT OF THE DISCLOSURE

A gate electrode of an n-type MIS transistor includes a first metal-containing film, which is formed in contact with a gate insulation film and has a Fermi level on a conductive band side from a substantial center of a band gap of a semiconductor substrate, and a second metal-containing film formed on the first metal-containing film and having a lower resistance than the first metal-containing film. A gate electrode of a p-type MIS transistor includes a conductive coating film, which is formed in contact with the gate insulation film and has a Fermi level on a valence band side from a substantial center of the band gap of the semiconductor substrate, and the second metal-containing film formed on the conductive coating film and having a lower resistance than the conductive coating film.